

SMN1A - SMN1M

PRV : 50 - 1000 Volts
Io : 1.0 Ampere

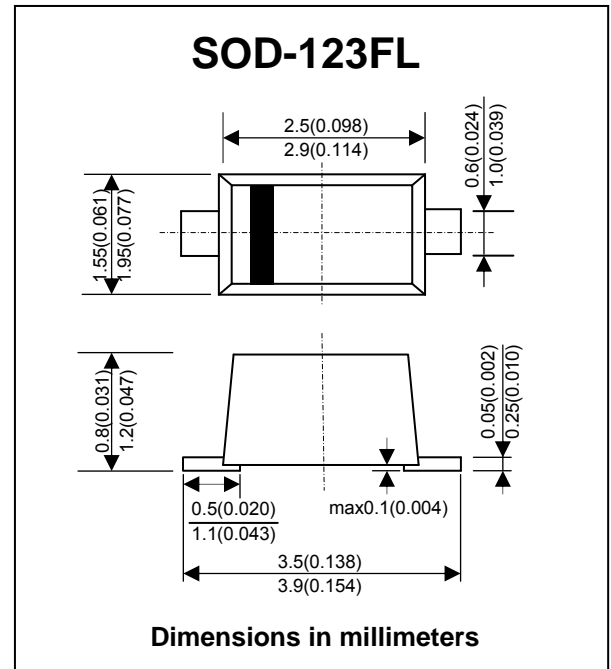
FEATURES :

- * Glass passivated junction chip
- * High current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * **Pb Free / RoHS Compliant**

MECHANICAL DATA :

- * Case: JEDEC SOD-123FL, molded plastic over passivated chip
- * Terminals: Solder Plated, solderable per MIL-STD-750, Method 2026
- * Polarity: Color band denotes cathode end
- * Mounting position : Any
- * Weight: 0.02 gram (Approximate)

GLASS PASSIVATED JUNCTION SILICON SURFACE MOUNT



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.

RATING	SYMBOL	SMN1A	SMN1B	SMN1D	SMN1G	SMN1J	SMN1K	SMN1M	UNIT
Marking		NA	NB	ND	NG	NJ	NK	NM	
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Current $T_a = 75\text{ }^\circ\text{C}$	$I_{F(AV)}$	1.0							A
Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on rated load (JEDEC Method)	I_{FSM}	30							A
Maximum Forward Voltage at $I_F = 1.0\text{ Amp.}$	V_F	1.0							V
Maximum DC Reverse Current $T_a = 25\text{ }^\circ\text{C}$ at rated DC Blocking Voltage $T_a = 100\text{ }^\circ\text{C}$	I_R	5.0							μA
	$I_{R(H)}$	50							μA
Typical Junction Capacitance (Note1)	C_J	8.0							pF
Operation Junction Temperature Range	T_J	- 55 to + 150							$^\circ\text{C}$
Storage Temperature Range	T_{STG}	- 55 to + 150							$^\circ\text{C}$

Note : (1) Measured at 1.0 MHz and applied reverse voltage of 4.0Vbc.

RATING AND CHARACTERISTIC CURVES (SMN1A - SMN1M)

FIG.1 - DERATING CURVE CURRENT

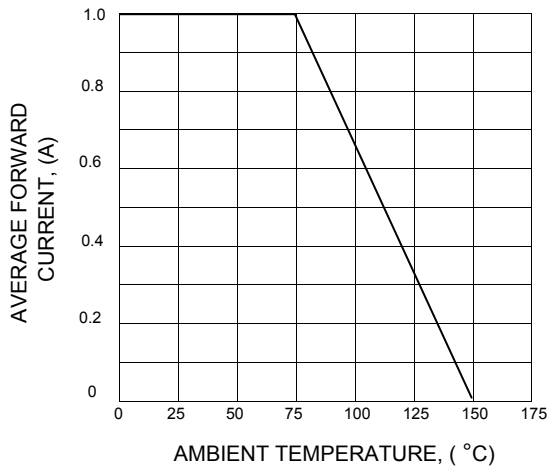


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

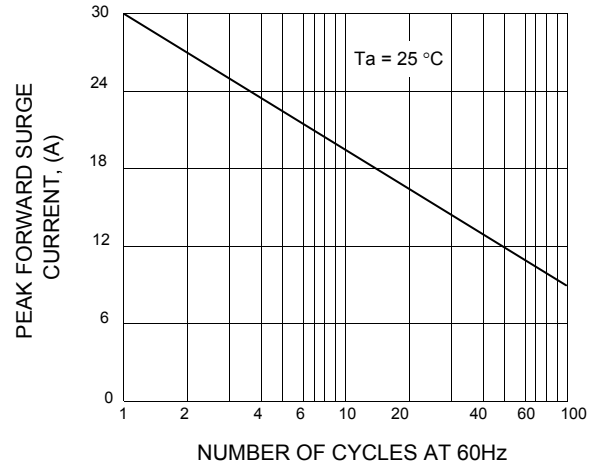


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

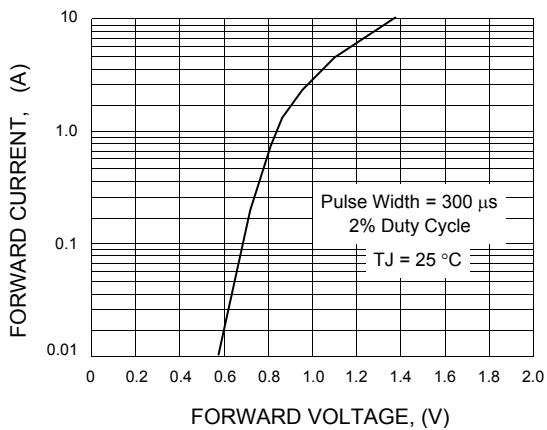


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

